

### General Description

The QM09N65P is the highest performance N-ch MOSFETs with specialized high voltage technology, which provide excellent RDSON and gate charge for most of the SPS, Charger ,Adapter and lighting applications .

The QM09N65P meet the RoHS and Green Product requirement , 100% EAS guaranteed with full function reliability approved.

### Features

- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

### Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	650	V
$V_{GS}$	Gate-Source Voltage	$\pm 30$	V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^1$	9	A
$I_D@T_C=100^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^1$	7	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	18	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	34	mJ
$I_{AS}$	Avalanche Current	8	A
$P_D@T_C=25^{\circ}C$	Total Power Dissipation <sup>4</sup>	156	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^{\circ}C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^{\circ}C$

### Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient (Steady State) <sup>1</sup>	---	62	$^{\circ}C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	---	0.8	$^{\circ}C/W$

### Product Summary

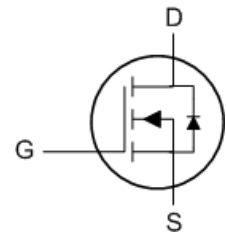
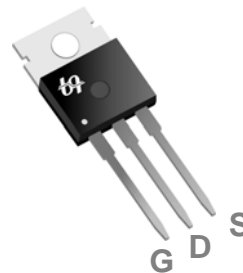


BVDSS	RDSON	ID
650V	1.1 $\Omega$	9 A

### Applications

- High efficient switched mode power supplies
- Electronic lamp ballast
- LCD TV/ Monitor
- Adapter

### TO220 Pin Configuration



**Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V$ , $I_D=250\mu A$	650	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	$BV_{DSS}$ Temperature Coefficient	Reference to $25^\circ\text{C}$ , $I_D=1\text{mA}$	---	0.7	---	V/ $^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=10V$ , $I_D=2.75A$	---	0.95	1.1	$\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$ , $I_D=250\mu A$	2	---	5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-8.9	---	mV/ $^\circ\text{C}$
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=520V$ , $V_{GS}=0V$ , $T_J=25^\circ\text{C}$	---	---	2	$\mu A$
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 30V$ , $V_{DS}=0V$	---	---	$\pm 100$	nA
gfs	Forward Transconductance	$V_{DS}=10V$ , $I_D=2.75A$	---	7	---	S
$Q_g$	Total Gate Charge (10V)	$V_{DS}=520V$ , $V_{GS}=10V$ , $I_D=1A$	---	33	---	nC
$Q_{gs}$	Gate-Source Charge		---	9.5	---	
$Q_{gd}$	Gate-Drain Charge		---	9.8	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=300V$ , $V_{GS}=10V$ , $R_G=10\Omega$ , $I_D=1A$	---	19	---	ns
$T_r$	Rise Time		---	19.4	---	
$T_{d(off)}$	Turn-Off Delay Time		---	56.4	---	
$T_f$	Fall Time		---	38	---	
$C_{iss}$	Input Capacitance	$V_{DS}=25V$ , $V_{GS}=0V$ , $F=1\text{MHz}$	---	1538	---	pF
$C_{oss}$	Output Capacitance		---	100	---	
$C_{rss}$	Reverse Transfer Capacitance		---	1.9	---	

**Guaranteed Avalanche Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy <sup>5</sup>	$V_{DD}=50V$ , $L=1\text{mH}$ , $I_{AS}=3.5A$	6.6	---	---	mJ

**Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$I_S$	Continuous Source Current <sup>1,6</sup>	$V_G=V_D=0V$ , Force Current	---	---	9	A
$I_{SM}$	Pulsed Source Current <sup>2,6</sup>		---	---	18	A
$V_{SD}$	Diode Forward Voltage <sup>2</sup>	$V_{GS}=0V$ , $I_S=1A$ , $T_J=25^\circ\text{C}$	---	---	1	V
$t_{rr}$	Reverse Recovery Time	$I_F=1A$ , $dI/dt=100A/\mu s$ , $T_J=25^\circ\text{C}$	---	158	---	nS
$Q_{rr}$	Reverse Recovery Charge		---	677	---	nC

Note :

1. The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
2. The data tested by pulsed, pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$
3. The EAS data shows Max. rating. The test condition is  $V_{DD}=50V$ ,  $V_{GS}=10V$ ,  $L=1\text{mH}$ ,  $I_{AS}=8A$
4. The power dissipation is limited by  $150^\circ\text{C}$  junction temperature
5. The Min. value is 100% EAS tested guarantee.
6. The data is theoretically the same as  $I_D$  and  $I_{DM}$ , in real applications, should be limited by total power dissipation.

### Typical Characteristics

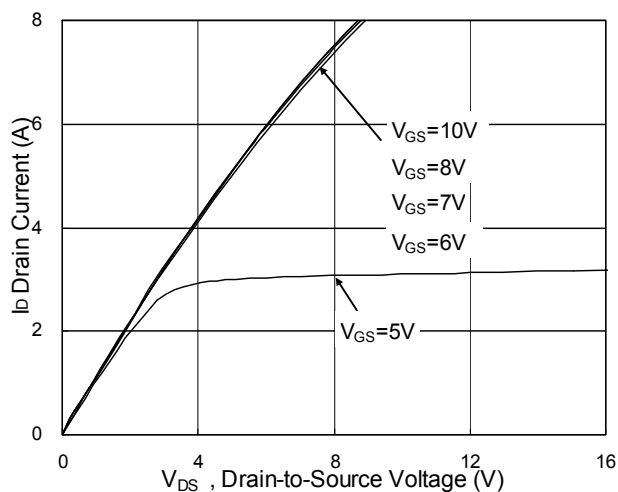


Fig.1 Typical Output Characteristics

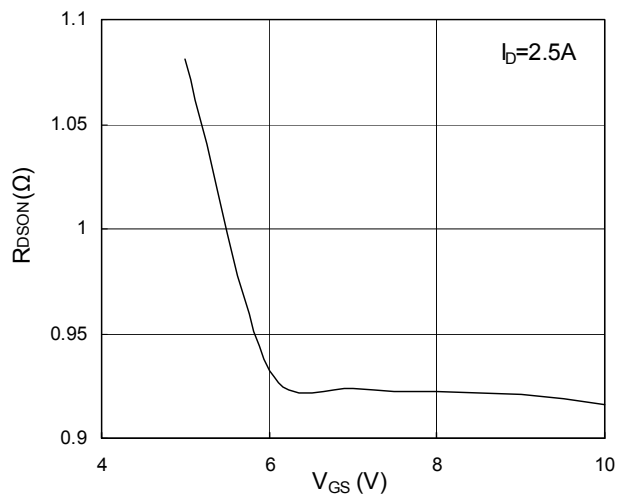


Fig.2 On-Resistance vs. G-S Voltage

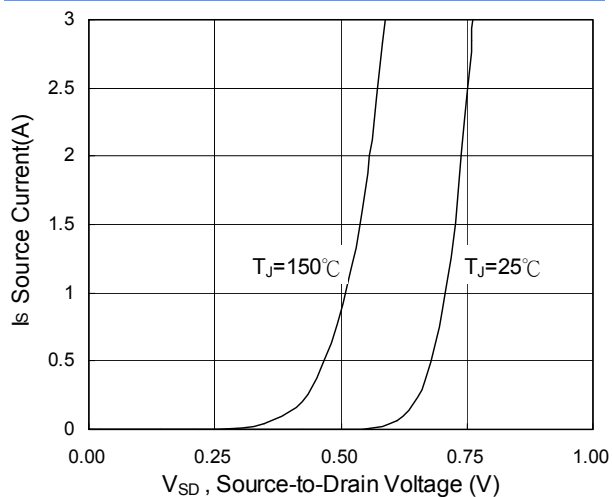


Fig.3 Forward Characteristics of Reverse

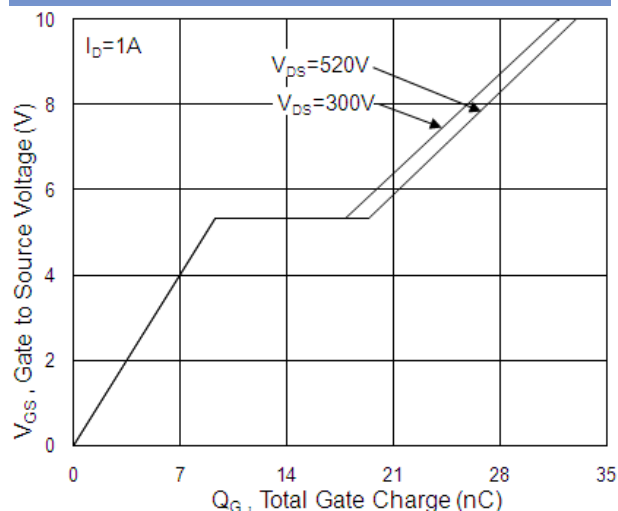


Fig.4 Gate-Charge Characteristics

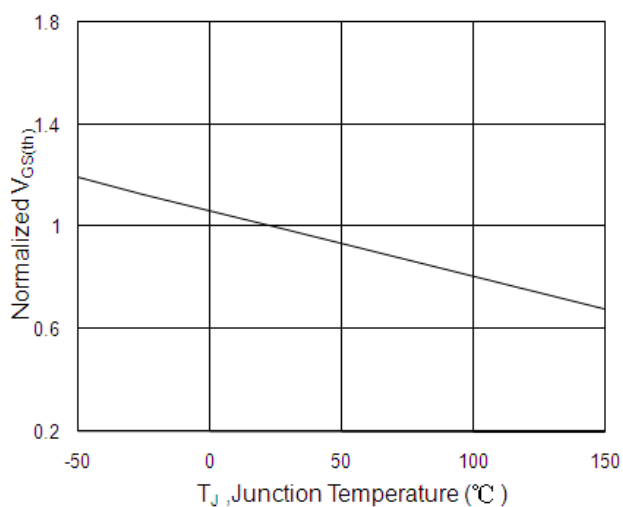


Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$

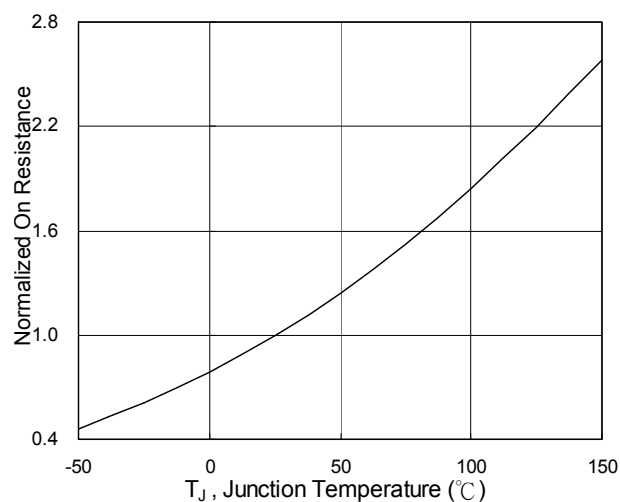


Fig.6 Normalized  $R_{DS(on)}$  vs.  $T_J$

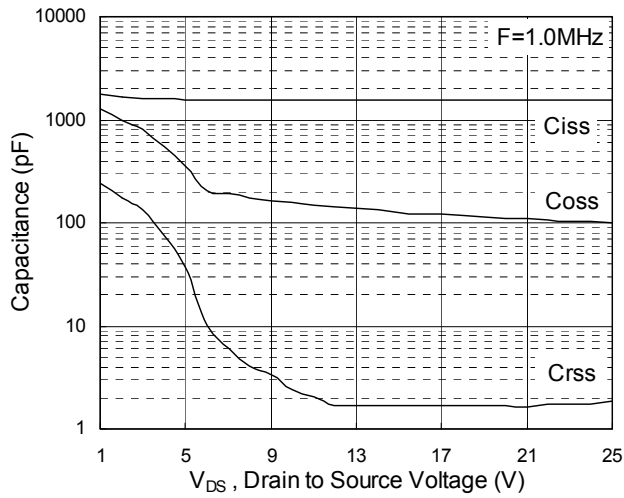


Fig.7 Capacitance

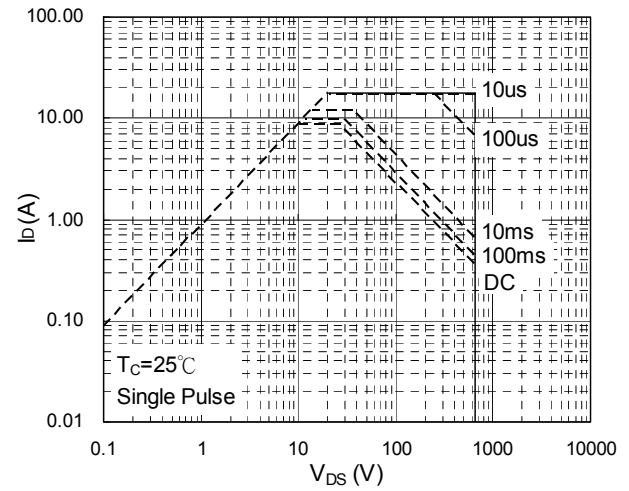


Fig.8 Safe Operating Area

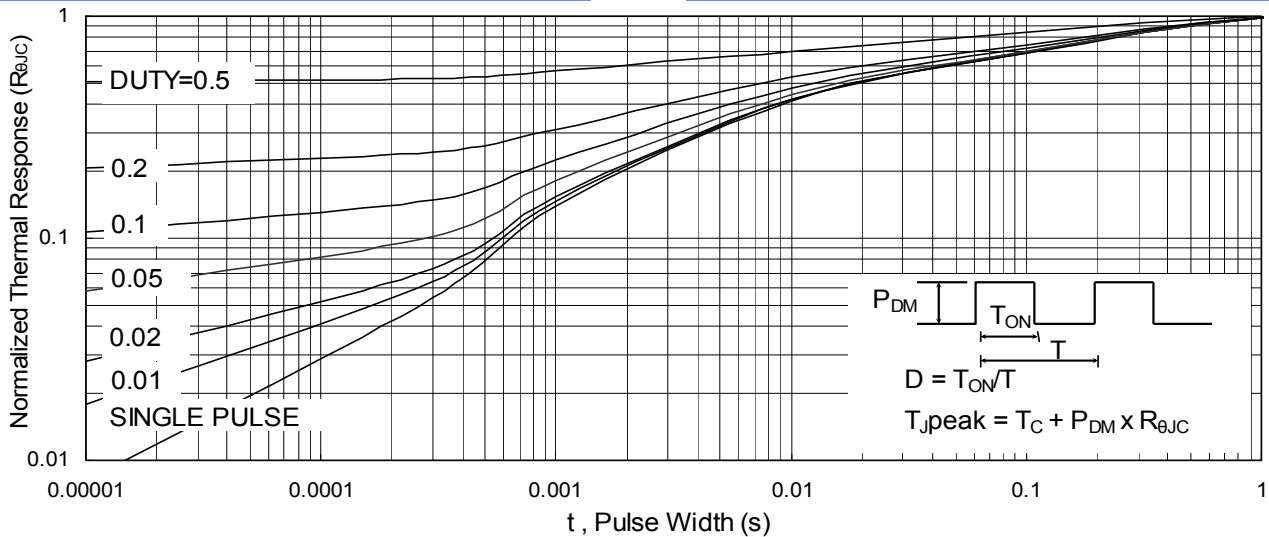


Fig.9 Normalized Maximum Transient Thermal Impedance

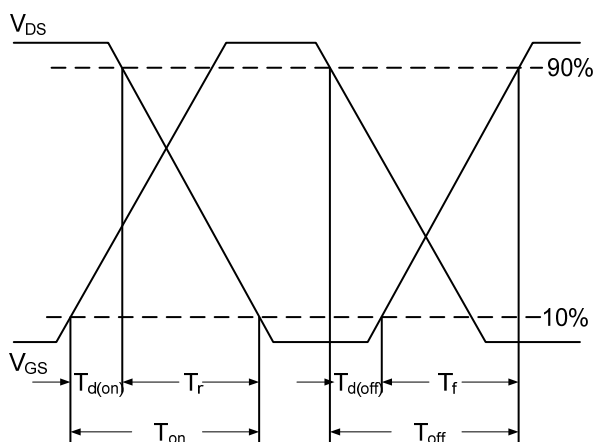


Fig.10 Switching Time Waveform

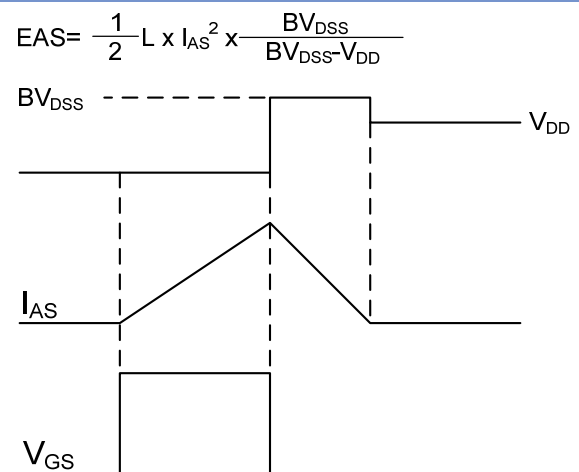


Fig.11 Unclamped Inductive Switching Waveform